Abstract Submitted
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p-type and n-type amorphous thin films for solar cells PRATHEESH JAKKALA, None — The presentation is about making and characterizing the p-type and n-type amorphous semiconductor thin films suitable for solar cells. Indium Gallium Nitride(InGaN), copper oxide thin films of different thickness are deposited on glass substrate using rf sputtering method at different temperatures. p-type nature of copper oxide and n-type nature of InGaN is verified using Hall effect measurement system, resistivity and conductivity values, I-V curves has been recorded. Band gap values has been measured using UV spectro photometer. Experimental values are very close to theoretical values. Composition of InGaN has been found using EDX measurement.

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None

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